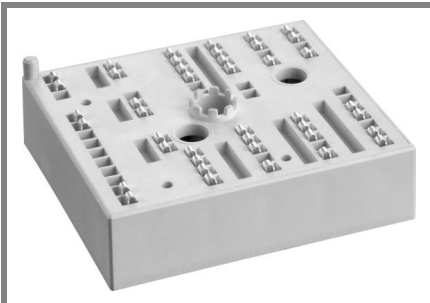


# SKiiP 25AC125V10



MiniSKiiP<sup>®</sup> 2

## 3-phase bridge inverter

### SKiiP 25AC125V10

#### Target Data

#### Features

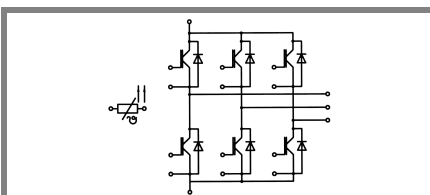
- Ultrafast NPT IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

#### Typical Applications

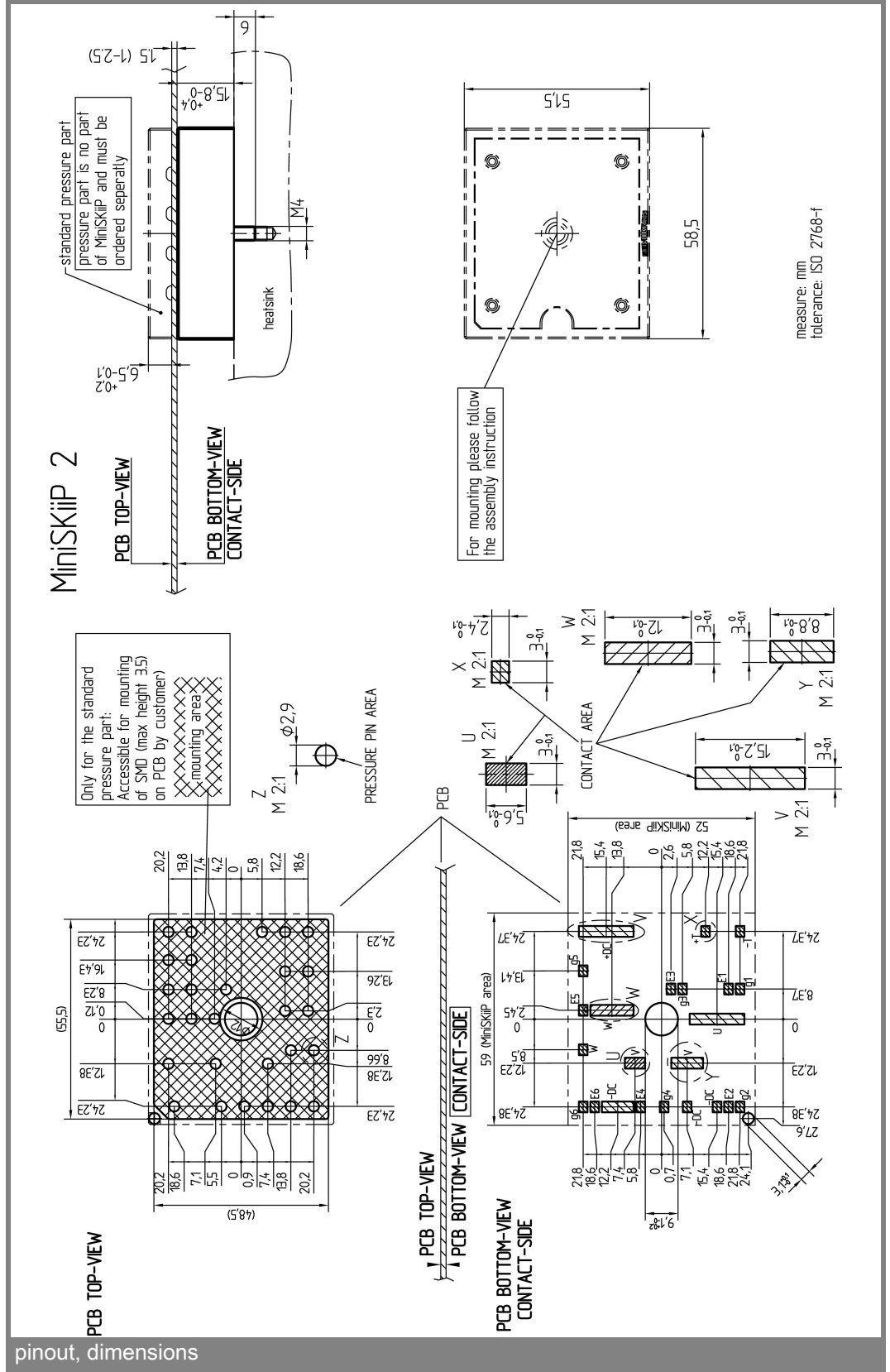
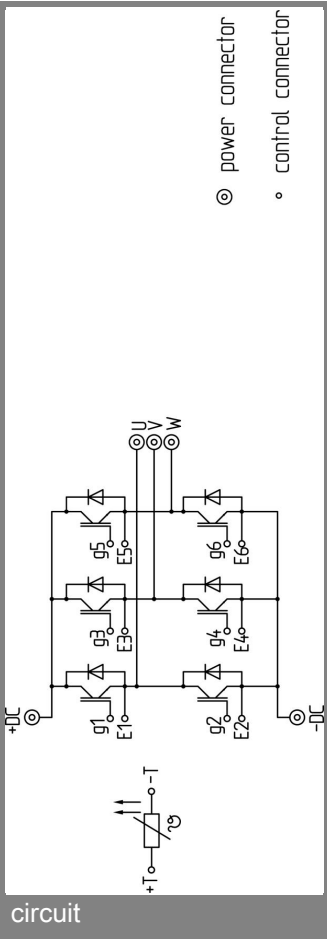
- Inverter up to 20 kVA
- Typical motor power 11 kW

Absolute Maximum Ratings		$T_s = 25\text{ }^\circ\text{C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT - Inverter</b>			
$V_{CES}$		1200	V
$I_C$	$T_s = 25\text{ (70) }^\circ\text{C}$	52 (39)	A
$I_{CRM}$	$T_s = 25\text{ (70) }^\circ\text{C}$ , $t_p \leq 1\text{ ms}$	104 (78)	A
$V_{GES}$		$\pm 20$	V
$T_j$		- 40 ... + 150	$^\circ\text{C}$
<b>Diode - Inverter</b>			
$I_F$	$T_s = 25\text{ (70) }^\circ\text{C}$	67 (50)	A
$I_{FRM}$	$T_s = 25\text{ (70) }^\circ\text{C}$ , $t_p \leq 1\text{ ms}$	134 (100)	A
$T_j$		- 40 ... + 150	$^\circ\text{C}$
$I_{tRMS}$	per power terminal (20 A / spring)	100	A
$T_{stg}$	$T_{op} \leq T_{stg}$	- 40 ... + 125	$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ }^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT - Inverter</b>					
$V_{CEsat}$	$I_C = 50\text{ A}$ , $T_j = 25\text{ (125) }^\circ\text{C}$		3,5 (4,1)	3,9 (4,5)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 2\text{ mA}$	4,5	5,5	6,5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) }^\circ\text{C}$		1,5 (1,8)	1,7 (2)	V
$r_T$	$T_j = 25\text{ (125) }^\circ\text{C}$		40 (46)	44 (50)	m $\Omega$
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		3,1		nF
$C_{oes}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		0,4		nF
$C_{res}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		0,4		nF
$R_{th(j-s)}$	per IGBT		0,5		K/W
$t_{d(on)}$	under following conditions		100		ns
$t_r$	$V_{CC} = 600\text{ V}$ , $V_{GE} = \pm 15\text{ V}$		60		ns
$t_{d(off)}$	$I_C = 50\text{ A}$ , $T_j = 125\text{ }^\circ\text{C}$		400		ns
$t_f$	$R_{Gon} = R_{Goff} = 12\text{ }^\circ\Omega$		20		ns
$E_{on}$	inductive load		5,9		mJ
$E_{off}$			3,1		mJ
<b>Diode - Inverter</b>					
$V_F = V_{EC}$	$I_F = 50\text{ A}$ , $T_j = 25\text{ (125) }^\circ\text{C}$		2 (1,8)	2,5 (2,3)	V
$V_{(TO)}$	$T_j = 25\text{ (125) }^\circ\text{C}$		1,3 (1)	1,5 (1,2)	V
$r_T$	$T_j = 25\text{ (125) }^\circ\text{C}$		14 (16)	20 (22)	m $\Omega$
$R_{th(j-s)}$	per diode		0,7		K/W
$I_{RRM}$	under following conditions		40		A
$Q_{rr}$	$I_F = 50\text{ A}$ , $V_R = 600\text{ V}$		8		$\mu\text{C}$
$E_{rr}$	$V_{GE} = 0\text{ V}$ , $T_j = 125\text{ }^\circ\text{C}$		2		mJ
	$di_F/dt = 800\text{ A}/\mu\text{s}$				
<b>Temperature Sensor</b>					
$R_{ts}$	3 %, $T_r = 25\text{ (100) }^\circ\text{C}$		1000(1670)		$\Omega$
<b>Mechanical Data</b>					
m			65		g
$M_s$	Mounting torque	2		2,5	Nm



AC



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.